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Vishay Siliconix

# Automotive N-Channel 30 V (D-S) 175 °C MOSFET



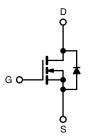
PRODUCT SUMMARY					
V <sub>DS</sub> (V)	30				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.00077				
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS} = 4.5 \text{ V}$	0.00128				
I <sub>D</sub> (A)	410				
Configuration	Single				
Package	PowerPAK SO-8L				

#### **FEATURES**

- TrenchFET® Gen IV power MOSFET
- AEC-Q101 qualified
- 100 % R<sub>q</sub> and UIS tested
- Q<sub>gd</sub>/Q<sub>gs</sub> ratio < 1 optimizes switching characteristics</li>







N-Channel MOSFET

<b>ABSOLUTE MAXIMUM RATINGS</b> ( $T_C = 25$ °C, unless otherwise noted)						
PARAMETER		SYMBOL	LIMIT	UNIT		
Drain-source voltage		V <sub>DS</sub>	30	V		
Gate-source voltage		$V_{GS}$	± 20			
Continuous drain current	T <sub>C</sub> = 25 °C	-	410			
	T <sub>C</sub> = 125 °C	I <sub>D</sub>	331			
Continuous source current (diode conduction	I <sub>S</sub>	454	Α			
Pulsed drain current <sup>a</sup>		I <sub>DM</sub>	410			
Single pulse avalanche current	L = 0.1 mH	I <sub>AS</sub>	55.5			
Single pulse avalanche energy	L=0.11IIII	E <sub>AS</sub>	154	mJ		
Maximum power dissipation <sup>a</sup>	T <sub>C</sub> = 25 °C	В	500	W		
	T <sub>C</sub> = 125 °C	$P_{D}$	166			
Operating junction and storage temperature range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C		
Soldering recommendations (peak temperature) <sup>c</sup>			260			

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	LIMIT	UNIT		
Junction-to-ambient	PCB mount b	$R_{thJA}$	42	°C/W		
Junction-to-case (drain)			0.3	C/VV		

### Notes

- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %
- b. When mounted on 1" square PCB (FR4 material)
- c. See solder profile (www.vishay.com/doc?73257). The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static								
Drain-source breakdown voltage	V <sub>DS</sub>	$V_{GS} = 0$ , $I_D = 250 \mu A$		30	-	-	V	
Gate-source threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$		2.0	2.5	V	
Gate-source leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	± 100	nA	
Zero gate voltage drain current		$V_{GS} = 0 V$	V <sub>DS</sub> = 40 V	-	-	1		
	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 30 V, T <sub>J</sub> = 125 °C	-	-	50	μΑ	
		$V_{GS} = 0 V$	V <sub>DS</sub> = 30 V, T <sub>J</sub> = 175 °C	-	-	250		
On-state drain current a	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V	$V_{DS} \ge 5 V$	30	-	-	Α	
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 15 A	-	0.00066	0.00077		
Drain accurac on state registeres 3		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 15 A, T <sub>J</sub> = 125 °C	-	-	0.00130	Ω	
Drain-source on-state resistance a	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 15 A, T <sub>J</sub> = 175 °C	-	-	0.00150		
		V <sub>GS</sub> = 4.5 V	I <sub>D</sub> = 15 A, T <sub>J</sub> = 175 °C	-	0.0010	0.00128		
Forward transconductance b	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 10 A		-	55	-	S	
Dynamic <sup>b</sup>								
Input capacitance	C <sub>iss</sub>		V <sub>DS</sub> = 25 V, f = 1 MHz	-	6984	9778	pF	
Output capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$		-	1774	2484		
Reverse transfer capacitance	C <sub>rss</sub>			-	186	261		
Total gate charge <sup>c</sup>	Qg			-	129	195		
Gate-source charge c	Q <sub>gs</sub>	$V_{GS} = 10 \text{ V}$	$V_{GS} = 10 \text{ V}$ $V_{DS} = 15 \text{ V}, I_D = 15 \text{ A}$		22	-	nC	
Gate-drain charge <sup>c</sup>	Q <sub>gd</sub>			-	25	-		
Gate resistance	R <sub>g</sub>	f = 1 MHz		0.8	1.7	2.6	Ω	
Turn-on delay time <sup>c</sup>	t <sub>d(on)</sub>		$V_{DD}$ = 15 V, $R_L$ = 1.0 $\Omega$ $I_D \cong$ 15 A, $V_{GEN}$ = 10 V, $R_g$ = 1 $\Omega$		15	23	ns	
Rise time <sup>c</sup>	t <sub>r</sub>	V <sub>DD</sub> =			18	29		
Turn-off delay time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong 15 A$ ,			55	83		
Fall time <sup>c</sup>	t <sub>f</sub>	1		-	19	29		
Source-Drain Diode Ratings and Char-	acteristics <sup>b</sup>							
Pulsed current <sup>a</sup>	I <sub>SM</sub>			-	-	1816	Α	
Forward voltage	V <sub>SD</sub>	I <sub>F</sub> = 15 A, V <sub>GS</sub> = 0 V		-	-	1.1	V	
Body diode reverse recovery time	t <sub>rr</sub>	I <sub>F</sub> = 10 A, di/dt = 100 A/μs		-	58	116	ns	
Body diode reverse recovery charge	Q <sub>rr</sub>			-	71	142	nC	
Reverse recovery fall time	ta			-	29	-	ns	
Reverse recovery rise time	t <sub>b</sub>			-	30	-		
Body diode peak reverse recovery current	I <sub>RM(REC)</sub>			-	-2.2	-	Α	

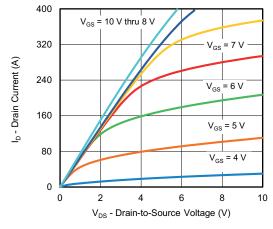
#### Notes

- a. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%$
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

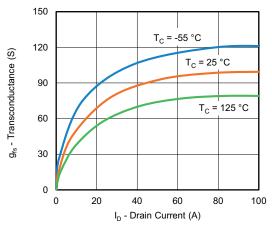
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



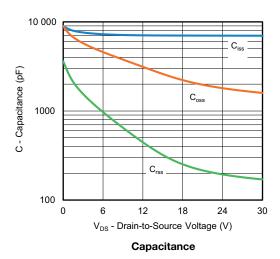
# **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)

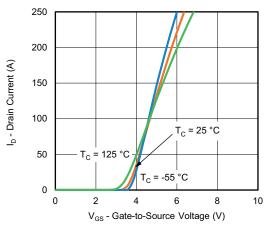


## **Output Characteristics**

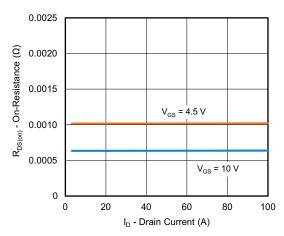


Transconductance

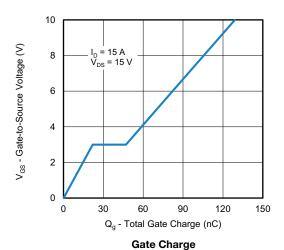




**Transfer Characteristics** 

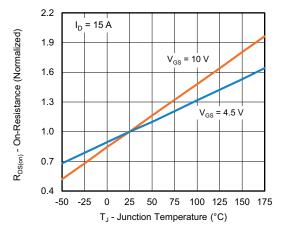


**On-Resistance vs. Drain Current** 

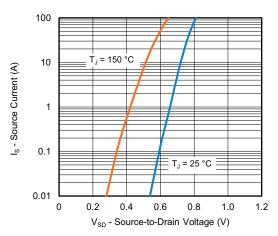




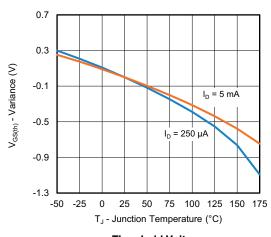
# **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



On-Resistance vs. Junction Temperature

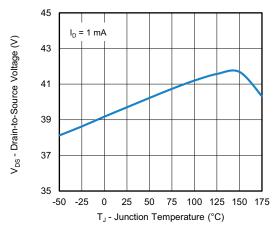


**Source Drain Diode Forward Voltage** 

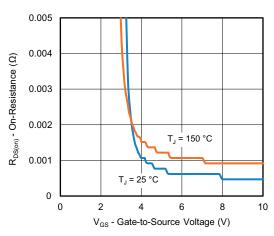


Threshold Voltage

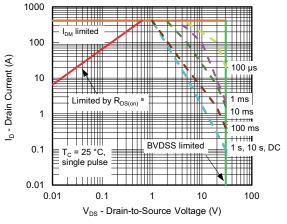
# Note $a. \ \ V_{GS} > minimum \ V_{GS} \ at \ which \ R_{DS(on)} \ is \ specified$



**Drain Source Breakdown vs. Junction Temperature** 



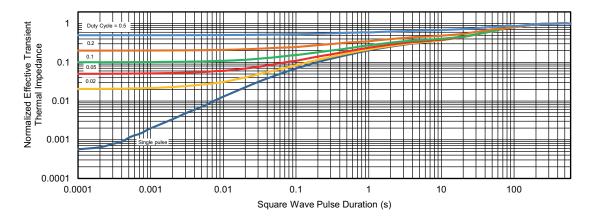
On-Resistance vs. Gate-to Source Voltage



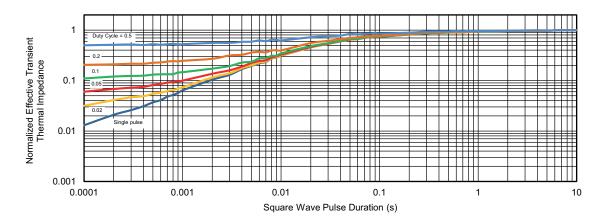
Safe Operating Area



## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



#### Normalized Thermal Transient Impedance, Junction-to-Ambient



#### Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

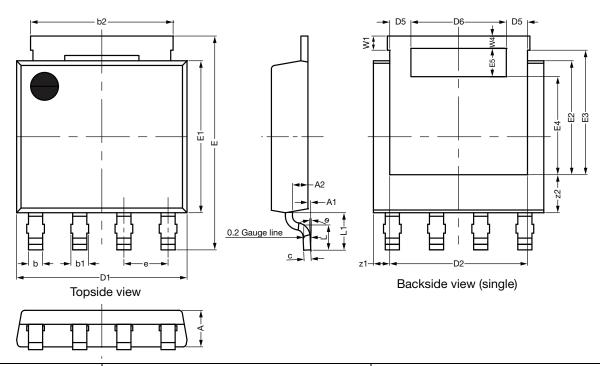
are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

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# PowerPAK® SO-8L Case Outline 3



DIM.	MILLIMETERS			INCHES			
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
A	1.00	1.05	1.10	0.039	0.041	0.043	
A1	0.00		0.127	0.000		0.005	
A2	0.40	0.45	0.50	0.016	0.018	0.020	
b	0.33	0.41	0.49	0.013	0.016	0.019	
b1	0.43	0.51	0.59	0.017	0.020	0.023	
b2	4.00	4.10	4.20	0.157	0.161	0.165	
С	0.15	0.20	0.25	0.006	0.008	0.010	
D1	4.80	4.90	5.00	0.189	0.193	0.197	
D2	3.86	3.96	4.06	0.152	0.156	0.160	
D5	0.51	0.61	0.71	0.020	0.024	0.028	
D6	2.64	2.74	2.84	0.104	0.108	0.112	
е		1.27 BSC		0.050 BSC			
E	6.05	6.15	6.25	0.238	0.242	0.246	
E1	4.27	4.37	4.47	0.168	0.172	0.176	
E2	3.18	3.28	3.38	0.125	0.129	0.133	
E3	3.48	3.58	3.68	0.137	0.141	0.145	
E4	2.72	2.82	2.92	0.107	0.111	0.115	
E5	0.71	0.81	0.91	0.028	0.032	0.036	
L	0.62	0.72	0.82	0.024	0.028	0.032	
L1	0.92	1.07	1.22	0.036	0.042	0.048	
W1	0.31	0.41	0.51	0.012	0.016	0.020	
W4	0.31	0.36	0.41	0.012	0.014	0.016	
z1	0.37	0.47	0.57	0.015	0.019	0.022	
z2	0.99	1.09	1.19	0.039	0.043	0.047	
θ	0°		5°	0°		5°	

ECN: S19-0643-Rev. B, 05-Aug-2019

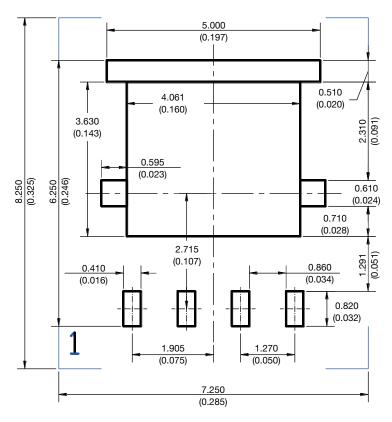
## DWG: 6067 **Note**

• Millimeter will govern

Revison: 05-Aug-2019 1 Document Number: 76666



## RECOMMENDED MINIMUM PAD FOR PowerPAK® SO-8L SINGLE



Recommended Minimum Pads Dimensions in mm (inches)



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